

GA06JT12-247 Information



Part Number GA06JT12-247

Manufacturer GeneSiC Semiconductor

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description TRANS SJT 1200V 6A TO-247AB

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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GA06JT12-247 Specifications

Manufacturer Part Number GA06JT12-247 Manufacturer GeneSiC Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series - FET Type - Technology SiC (Silicon Carbide Junction Transistor) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 6A (Tc) (90°C) Drive Voltage (Max Rds On, Min Rds On) - Vgs(th) (Max) @ Id - Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) Vds Vgs (Max) EV Pet Feature - Power Dissipation (Max) - Rds On (Max) @ Id, Vgs 220 mOhm @ 6A Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AB Package / Case TO-247-3		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-247-3Series-FET Type-TechnologySiC (Silicon Carbide Junction Transistor)Drain to Source Voltage (Vdss)1200VCurrent - Continuous Drain (Id) @ 25°C6A (Tc) (90°C)Drive Voltage (Max Rds On, Min Rds On)-Vgs(th) (Max) @ Id-Gate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds-Vgs (Max)-FET Feature-Power Dissipation (Max)-Rds On (Max) @ Id, Vgs220 mOhm @ 6AOperating Temperature175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247ABPackage / CaseTO-247-3	Manufacturer Part Number	GA06JT12-247
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Rds On (Max) @ Id, Vgs 220 mOhm @ 6A Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AB Package / Case TO-247-3	FET Feature	-
Operating Temperature 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AB Package / Case TO-247-3	Power Dissipation (Max)	-
Mounting Type Through Hole Supplier Device Package TO-247AB Package / Case TO-247-3	Rds On (Max) @ Id, Vgs	220 mOhm @ 6A
Supplier Device Package TO-247AB Package / Case TO-247-3	Operating Temperature	175°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
•	Supplier Device Package	TO-247AB
Report errors?	Package / Case	TO-247-3
		Report errors?

GA06JT12-247 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

GA06JT12-247 Payment Methods



















GA06JT12-247 Shipping Methods













If you have any question about GA06JT12-247, please do not hesitate to contact us!

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